

Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended) A semiconductor device, comprising:

an underlayer;

a base oxide film with first holes and formed on the underlayer;

a groove having a sidewall formed in said base oxide film around respective ones of said first holes;

a plurality of nitride film patterns, each having a hole pattern, respectively, formed on the base oxide film and directly connected to said first holes, respectively;

an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough a plurality of wiring grooves which each reaches part of an associated nitride film pattern including said hole patterns; and

wiring metal that fills said first holes, and said wiring grooves;

and wherein said nitride film patterns are separate from each other and have a shape and size that extends from the outside of their associated wiring groove.

Claim 2 (Original) A semiconductor device according to claim 1 wherein said nitride film pattern is formed with such a shape and size that surrounds the outside of said wiring groove with a gap from 0.2 to 1.0 μm .

Claim 3 (Currently Amended) A semiconductor device, comprising:

an underlayer;

a base oxide film with first holes formed on the underlayer;

a plurality of nitride film patterns on the base oxide film, the nitride film patterns having formed therethrough hole patterns, respectively, which are formed directly connected to and wider than said first holes respectively;

an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough a plurality of wiring grooves which each exposes part of the nitride film patterns including said hole patterns; and

wiring metal that fills part of each of the exposed nitride film patterns, each of said first ~~said~~ holes, each of said hole patterns, and each of said wiring grooves;

and wherein an outer shape of each of said nitride film patterns is substantially the same as the shape of the opening of each of said wiring grooves, an internal wall surface of each of said wiring grooves is tapered from the opening on an upper surface of said upper oxide film to upper surface of each of said nitride film patterns, and neighbouring nitride film patterns are separate from each other.

Claim 4 (Previously Amended) A semiconductor device, comprising:

an underlayer;

a base oxide film formed on the underlayer, the base oxide film having formed therethrough a plurality of first holes;

an upper oxide film provided on the base oxide film, the upper oxide film having formed therethrough wiring grooves which are connected to said first holes, respectively; and

barrier and wiring metal that fills each of said first holes and each of said wiring grooves, said barrier and wiring metal having a first portions on the base oxide film and second portions at a middle section of said upper oxide film above said first portions, and each of said first portions having a width W1 wide than a width W3 of each of the second portions.

Claim 5 (Original) A semiconductor device according to claim 1, wherein part of the upper surface of said underlayer constitutes the base wiring area, said hole reaches the base wiring area, and a dispersion protection film is formed only on said base wiring area outside the hole.

Claim 6 (Original) A semiconductor device according to claim 2, wherein part of the upper surface of said underlayer constitutes the base wiring area, said hole reaches the base wiring area, and a dispersion protection film is formed only on said base wiring area outside the hole.

Claim 7 (Original) A semiconductor device according to claim 3, wherein part of the upper surface of said underlayer constitutes the base wiring area, said hole reaches the base wiring area; and a dispersion protection film is formed only on said base wiring area outside the hole.

Claim 8 (Original) A semiconductor device according to claim 3, wherein part of the upper surface of said underlayer constitutes the base wiring area, and a dispersion protection film is formed only on said base wiring area outside the hole.

Claims 9-19 (Canceled)

Claim 20 (New) The semiconductor device of claim 1, wherein said nitride film patterns are formed in said groove and have a portion around said sidewall that is thicker than a portion in a bottom of said groove.

Claim 21 (New) The semiconductor device of claim 1, further comprising a sidewall film formed on the sidewall of said groove.

Claim 22 (New) The semiconductor device of claim 21, wherein said sidewall film has a higher etching selection ratio for an SiO₂ film than for a nitride film.